## **Supporting Information**

Improving photoelectrochemical performance of highly-ordered TiO<sub>2</sub> nanotube arrays with cosensitization of PbS and CdS quantum dots

Xiaojiao Zhang <sup>ab</sup>, Min Zeng <sup>a</sup>, Jiawei Zhang <sup>c</sup>, Aimin Song <sup>c</sup>, Shiwei Lin <sup>ac</sup>\*

<sup>a</sup> Key Laboratory of Ministry of Education for Advanced Materials in Tropical Island Resources, College of Materials and Chemical Engineering, Hainan University, Haikou 570228, China
<sup>b</sup> School of Applied Science and Technology, Hainan Tropical Ocean University, Sanya 572022, China
<sup>c</sup> School of Electrical and Electronic Engineering, University of Manchester,

Sackville Street Building, Manchester M13 9PL, UK

\* Corresponding author. Tel.: +86 898 66290185; fax: +86 898 66290185. E-mail address: linsw@hainu.edu.cn (S. Lin).



**Fig. S1** XRD patterns of the untreated TNTAs, TNTAs/PbS(5), TNTAs/CdS(5), TNTAs/CdS(5)/PbS(2)/CdS(5) and TNTAs/CdS(5)/PbS(2).



Fig. S2 TEM images of the pure TNTAs.



Fig. S3 Equivalent circuit used to simulate the Nyquist plots measured by EIS in the Randles-Ershler model.  $R_s$  is the electrolyte resistance, *CPE* is the capacitance phase element for the semiconductor/electrolyte interface, and  $R_{ct}$  is the charge transfer resistance across the interface.

Samples	$R_{ m s}/\Omega$	$R_{ m ct}/\Omega$	CPE / F
TNTAs/PbS(5)	64.8	452	1.2×10 <sup>-4</sup>
TNTAs/PbS(5)/CdS(5)	68.9	634	1.5×10 <sup>-4</sup>
TNTAs/PbS(5)/CdS(14	39.0	3580	1.8×10 <sup>-4</sup>
)			
TNTAs/CdS(14)	81.7	38500	1.7×10 <sup>-4</sup>

Table S1 EIS fitting results within the intermediate frequency (1~1kHz).